

*SPECIFICATION AMENDMENTS*

Replace the paragraph beginning at page 3, line 12 with:

Referring to the graph of Fig.25, when the reflectance of the low reflective film 8 is controlled within  $6\% \pm 1\%$ , it is seen that the thickness of the low reflective film 8 must be controlled with an accuracy of  $\pm 1\%$ , i.e., nearly  $\pm 3$  nm with respect to the design value of thickness  $d_a = 318.9$  nm. Such an accuracy of thickness is difficult to obtain by means of vacuum evaporation or ~~spattering~~ sputtering which is generally used for forming an optical thin film, resulting in a lower yield of manufacturing a semiconductor laser.